L	Hits	Search Text	DB	Time stamp
Number -	1192	@ad<=20010104 and 'heating substrate' and	USPAT;	2003/04/11
		'amorphous silicon'	US-PGPUB;	13:46
			EPO; JPO; DERWENT;	
	943	(4420 (400)) 0077	IBM_TDB	
_	943	((438/486) or (438/482)).CCLS.	USPAT; US-PGPUB;	2002/10/03
			EPO; JPO;	
			DERWENT; IBM TDB	
-	71	(((438/486) or (438/482)).CCLS.) and	USPAT;	2002/10/03
		@ad<=20010104 and 'heating substrate' and 'amorphous silicon'	US-PGPUB; EPO; JPO;	13:00
			DERWENT;	
-	2	(@ad<=20010104 and 'heating substrate'	IBM_TDB USPAT;	2002/10/03
		and 'amorphous silicon') and	US-PGPUB;	13:18
		@ad<=20010104 and 'heating substrate' and 'amorphous silicon' and MILC	EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	(((438/486) or (438/482)).CCLS.) and MILC and 'low temperature'	USPAT; US-PGPUB;	2002/10/03
		The sompositions	EPO; JPO;	13.00
			DERWENT; IBM TDB	}
-	2	(@ad<=20010104 and 'heating substrate'	USPAT;	2002/10/03
		and 'amorphous silicon') and MILC and 'low temperature'	US-PGPUB; EPO; JPO;	13:06
		10W Competatore	DERWENT;	
_	0	@ad<=20010104 and 'amorphous silicon'	IBM_TDB USPAT;	2003/11/07
_		with 'metal layer' and 'heating' with	US-PGPUB;	12:01
		'while depositing'	EPO; JPO; DERWENT;	
			IBM TDB	
-	181	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'	USPAT; US-PGPUB;	2002/10/03
		with metal layer and heating	EPO; JPO;	13.11
Ì			DERWENT; IBM TDB	
-	109	(@ad<=20010104 and 'amorphous silicon'	USPAT;	2002/10/03
		with 'metal layer' and 'heating') and 'depositing'	US-PGPUB; EPO; JPO;	13:11
		depositing	DERWENT;	
	14	@ad<=20010104 and 'amorphous silicon'	IBM_TDB USPAT;	2002/10/03
- I	. 14	with 'metal layer' and 'heating' with	US-PGPUB;	13:11
		'depositing'	EPO; JPO; DERWENT;	
ļ			IBM_TDB	
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and	USPAT; US-PGPUB;	2002/10/24 13:10
		@ad<=20010104 and 'amorphous silicon' and	EPO; JPO;	13:10
		MILC	DERWENT;	
-	303	(((438/486) or (438/482)).CCLs.) and 'low	IBM_TDB USPAT;	2002/10/03
		temperature'	US-PGPUB;	13:37
-			EPO; JPO; DERWENT;	1
		(//420/406) /420/403))	IBM_TDB	0000 (10 (00
-	52	(((438/486) or (438/482)).CCLS.) and 'low temperature' and 'heating substrate'	USPAT; US-PGPUB;	2002/10/03
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	@ad<=20010104 and heating adj1 substrate	USPAT;	2002/10/24
		with depositing same metal and MILC	US-PGPUB; EPO; JPO;	13:51
			DERWENT;	
			IBM TDB	

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-	58	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO;	2003/11/07
			DERWENT; IBM TDB	
-	0	@ad<=20010104 and heating adjl substrate adjl while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO;	2002/10/24 13:54
			DERWENT; IBM_TDB	
-	0	@ad<=20010104 and heat adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO;	2002/10/24
1	3		DERWENT; IBM TDB	2002/10/24
-	3	@ad<=20010104 and heat adjl substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	13:56
	74	0-d (-20010104 and hearth a right nitration	IBM_TDB	2002/10/24
	/4	<pre>@ad<=20010104 and heating adj1 substrate same 'depositing metal'</pre>	USPAT; US-PGPUB; EPO; JPO;	2002/10/24
			DERWENT; IBM_TDB	
-	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB;	2002/10/24 14:16
1			EPO; JPO; DERWENT; IBM TDB	
-	191	<pre>@ad<=20010104 and 'amorphous silicon' same 'heating substrate'</pre>	USPĀT; US-PGPUB;	2002/10/24 15:55
}			EPO; JPO; DERWENT; IBM TDB	
-	12	<pre>@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'</pre>	USPĀT; US-PGPUB; EPO; JPO;	2002/10/24 15:40
			DERWENT; IBM TDB	
-	3778	((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.	USPAT; US-PGPUB;	2002/10/24 15:42
			EPO; JPO; DERWENT; IBM TDB	
-	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and	USPĀT; US-PGPUB;	2002/10/24 15:56
		@ad<=20010104 and 'heating substrate'	EPO; JPO; DERWENT; IBM TDB	
-	2	"20020137310"	USPAT; US-PGPUB;	2003/11/07 11:55
			EPO; JPO; DERWENT;	
-	447	@ad<=20010104 and low adj temperature adj crystallization	IBM_TDB USPAT; US-PGPUB;	2003/04/11 14:35
		-	EPO; JPO; DERWENT; IBM TDB	
-	318928	(("257") or ("438")).CLAS.	USPAT; US-PGPUB;	2003/04/11 13:59
			EPO; JPO; DERWENT; IBM TDB	
-	124	(@ad<=20010104 and low adj temperature adj crystallization) and 'nickel'	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 14:13
			DERWENT; IBM TDB	

-	1	("6524662").PN.	USPAT;	2003/04/11
1			US-PGPUB;	14:07
			EPO; JPO; DERWENT;	1
İ	1		IBM_TDB	1
l -	28	(@ad<=20010104 and low adj temperature	USPAT;	2003/04/11
		adj crystallization) and heat adj	US-PGPUB;	14:14
1		substrate and 'nickel'	EPO; JPO;	1
1			DERWENT;	1
1			IBM TDB	1
-	9		USPAT;	2003/04/11
}		'heat' same 'substrate'	US-PGPUB;	14:39
1			EPO; JPO;	1
1			DERWENT;	} 1
l _	6	@ad<=20010104 and 'heated' with	IBM_TDB USPAT;	2003/04/11
1	1 °	'substrate' same deposit adj nickel	US-PGPUB;	14:40
		Jubberate Jame deposit adj mreker	EPO; JPO;	11.10
1]		DERWENT;]
1			IBM TDB	[
-	62	@ad<=20010104 and MILC	USPAT;	2003/11/07
1			US-PGPUB;	11:26
1			EPO; JPO;	
1	1		DERWENT;	
1_	3	("6534663") DM	IBM_TDB	2003/11/03
-	1 3	("6524662").PN.	USPAT;	2003/11/07
1			US-PGPUB; EPO; JPO;	11:22
}	1		DERWENT;	1
	1		IBM TDB	1
-	24	@ad<=20010104 and Joo-seung.in.	USPAT;	2003/11/07
i		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	11:27
			EPO; JPO;	1
			DERWENT;	1 1
	1		IBM_TDB]
-	39	Joo-seung-ki.in.	USPAT;	2003/11/07
			US-PGPUB;	11:27
1	Į.		EPO; JPO; DERWENT;	!!!
1			IBM TDB	1 1
_	2	("6097037").PN.	USPAT;	2003/11/07
	1	,, ,	US-PGPUB;	11:57
1	1		EPO; JPO;	1
1	1		DERWENT;	1
1	1		IBM_TDB	
-	231		USPAT;	2003/11/07
1	1	same 'nickel' same 'sputtering'	US-PGPUB;	12:02
1	l		EPO; JPO; DERWENT;	[
	1		IBM TDB	
-	53	@ad<=20010104 and 'amorphous silicon'	USPAT;	2003/11/07
		with 'nickel' with 'sputtering'	US-PGPUB;	12:19
1	1		EPO; JPO;	
	1		DERWENT;	
1	_		IBM_TDB	
-	8	@ad<=20010104 and 'amorphous silicon'	USPAT;	2003/11/07
1	1	with 'nickel' with 'sputtering' with	US-PGPUB;	12:22
1]	'temperature'	EPO; JPO; DERWENT;	
1	1		IBM TDB]
-	222	@ad<=20010104 and 'sputtering' with	USPAT;	2003/11/07
		'temperature' same 'nickel'	US-PGPUB;	12:22
	l		EPO; JPO;	
			DERWENT;	
	ĺ		IBM_TDB	
-	100	@ad<=20010104 and 'sputtering' with	USPAT;	2003/11/07
1	1	'temperature' with 'nickel'	US-PGPUB;	12:27
	1		EPO; JPO; DERWENT;	
1	1		IBM TDB	
		<u> </u>	T TOP I TOB	

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-	5	<pre>@ad<=20010104 and 'nickel' with 'sputtering temperature'</pre>	USPAT; US-PGPUB;	2003/11/07 12:49
			EPO; JPO; DERWENT;	
-	0	@ad<=20010104 and 'nickel' with	IBM_TDB USPAT;	2003/11/07
		'oxidation' adj1 'stable' with 'silicide'	US-PGPUB;	12:48
1	Ĭ		EPO; JPO;	
	ļ		DERWENT; IBM TDB	
-	6		USPAT;	2003/11/07
1	Ì	'oxidation' adj1 'stable'	US-PGPUB; EPO; JPO;	12:48
1	Į.		DERWENT;	
_	11	 @ad<=20010104 and 'nickel' same	IBM_TDB USPAT:	2003/11/07
1	11	'sputtering temperature'	US-PGPUB;	12:55
1	l .		EPO; JPO;	
	ľ		DERWENT; IBM TDB	
-	93	@ad<=20010104 and 'nickel' same	USPAT;	2003/11/07
1	İ	'oxidation temperature'	US-PGPUB; EPO; JPO;	12:56
ļ	Į.		DERWENT;	
-	31	@ad<=20010104 and 'nickel' with	IBM_TDB USPAT;	2003/11/07
1	1	'oxidation temperature'	US-PGPUB;	13:02
1	ì		EPO; JPO; DERWENT;	
			IBM TDB	
-	72	@ad<=20010104 and 'nickel' with 'silicidation'	USPAT; US-PGPUB;	2003/11/07 13:02
	İ	orizora de cron	EPO; JPO;	25.02
	ļ		DERWENT; IBM TDB	ļ
-	27	@ad<=20010104 and 'nickel' adj1	USPAT;	2003/11/07
1	Ì	'silicidation'	US-PGPUB; EPO; JPO;	13:04
	ì		DERWENT;	
	26	 @ad<=20010104 and 'nickel' adj1	IBM_TDB USPAT;	2003/11/07
	26	'silicidation' and 'temperature'	US-PGPUB;	13:04
	1		EPO; JPO; DERWENT;	
1	1		IBM TDB	
-	17	@ad<=20010104 and 'nickel' adjl	USPAT;	2003/11/07
		'silicidation' same 'temperature'	US-PGPUB; EPO; JPO;	13.13
	1		DERWENT;	
_	153	@ad<=20010104 and 'nickel' same 'silicon'	IBM_TDB USPAT;	2003/11/07
		with 'crystallized' same 'temperature'	US-PGPUB;	13:16
			EPO; JPO; DERWENT;	
		0 4 20010104 1 12 1 12	IBM_TDB	2002 (11 (07
_	64	<pre>@ad<=20010104 and 'nickel' same 'silicon' with 'crystallized' with 'temperature'</pre>	USPAT; US-PGPUB;	2003/11/07 13:16
			EPO; JPO;	
			DERWENT; IBM TDB	
-	2	("5614291").PN.	USPAT;	2003/11/07
			US-PGPUB; EPO; JPO;	13:22
			DERWENT;	
l			IBM TDB	li